



AOS Semiconductor Product Reliability Report

AOT10B65M2, rev B

Plastic Encapsulated Device

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Nov. 2017

This AOS product reliability report summarizes the qualification result for AOT10B65M2. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOT10B65M2 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 175°C , Vge=100% of Vgemax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HTRB	Temp = 175°C , Vce=80% of Vcemax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HAST	130°C , 85%RH, 33.3 psia, Vce = 80% of Vcemax up to 42V	96 hours	462 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vce = 80% of Vcemax up to 100V	1000 hours	462 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000 cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 175°C	1000 hours	693 pcs	0	JESD22-A103
IOL	Δ Tj = 100°C	8572 cycles	462 pcs	0	AEC Q101
Resistance to Solder Heat	Temp = 270°C	15 seconds	30 pcs	0	JESD22-B106

Note: The reliability data presents total of available generic data up to the published date.

II. Reliability Evaluation

FIT rate (per billion): 1.31

MTTF = 87340 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.31$

MTTF = $10^9 / \text{FIT} = 87340 \text{ years}$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	125 deg C	150 deg C	175 deg C
Af	758	256	95	38	9.7	2.9	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / \text{K}$